P12LF10SLKD

Power MOSFETs 100V, 12A, Dual N-channel

Feature

- N-channel
- Small SMD
- Dual type
- 4.5V Gate Drive
- Based on AEC-Q101
- Halogen free
- Pb free terminal
- RoHS:Yes

OUTLINE



Equivalent circuit



Absolute Maximum Ratings (unless otherwise specified : Tc=25°C, per FET)

Item	Symbol	Conditions	Ratings	Unit
Storage temperature	Tstg		-55 to 175	°C
Channel tempertature	Tch		-55 to 175	°C
Drain-source voltage	V _{DSS}		100	V
Gate-source voltage	V _{GSS}		±20	V
Continuous drain current(DC)	Ι _D		12	А
Continuous drain current(Peak)	I _{DP}	Pulse width 10µs, duty=1/100	36	А
Total power dissipation	PT		50	W
Single avalanche current	I _{AS}	Starting Tch=25°C Tch≦150°C	12	А
Single avalanche energy	E _{AS}	Starting Tch=25°C Tch≦150°C	16	mJ

* : See the original Specifications

Item	Symbol	Conditions	Ratings			11-2
			MIN	ТҮР	MAX	Unit
Drain-Source breakdown voltage	V _{(BR)DSS}	ID=1mA, VGS=0V	100			V
Zero gate voltage drain current	I _{DSS}	VDS=100V, VGS=0V			1	μA
Gate-source leakage current	I _{GSS}	VGS=±20V, VDS=0V			±0.1	μA
Forward transconductance	g _{fs}	ID=6A, VDS=10V	7			S
Static drain-source on-state resistance	R _{DS(ON)}	ID=6A, VGS=10V		0.034	0.042	Ω
Static drain-source on-state resistance	R _{DS(ON)}	ID=6A, VGS=4.5V		0.037	0.049	Ω
Gate threshold voltage	Vth	ID=1mA, VDS=10V	1.5	2	2.5	V
Source-drain diode forward voltage	V _{SD}	IS=12A, VGS=0V			1.5	V
Thermal resistance	Rth(j-c)	Junction to case			2.98	°C/W
Total gate charge	Qg	VDD=80V, VGS=10V, ID=12A		32		nC
Gate to source charge	Qgs	VDD=80V, VGS=10V, ID=12A		6.3		nC
Gate to drain charge	Qgd	VDD=80V, VGS=10V, ID=12A		8		nC
Input capacitance	Ciss	VDS=25V, VGS=0V, f=1MHz		1420		pF
Reverce transfer capacitnce	Crss	VDS=25V, VGS=0V, f=1MHz		53		pF
Output capacitance	Coss	VDS=25V, VGS=0V, f=1MHz		110		pF
Turn-on delay time	td(on)	ID=6A, RL=8.33Ω, VDD=50V, Rg=0Ω, VGS(+)=10V, VGS(-)=0V		8.5		ns
Rise time	tr	ID=6A, RL=8.33Ω, VDD=50V, Rg=0Ω, VGS(+)=10V, VGS(-)=0V		19		ns
Turn-off delay time	td(off)	ID=6A, RL=8.33Ω, VDD=50V, Rg=0Ω, VGS(+)=10V, VGS(-)=0V		24		ns
Fall time	tf	ID=6A, RL=8.33Ω, VDD=50V, Rg=0Ω, VGS(+)=10V, VGS(-)=0V		4.5		ns
Diode reverse recovery time	trr	IF=12A, VGS=0V, di/dt=100A/µs		52		ns
Diode reverse recovery charge	Qrr	IF=12A, VGS=0V, di/dt=100A/µs		90		nC

* : See the original Specifications

CHARACTERISTIC DIAGRAMS



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unit:mm



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